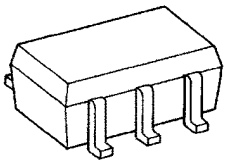
TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7PA17FU

Dual Schmitt Buffer

Features

- Operating voltage range: V_{CC} = 1.8~3.6 V
- High-speed operation: t_{pd} = 4.0 ns (max) at V_{CC} = 3.0~3.6 V
  t_{pd} = 4.3 ns (max) at V_{CC} = 2.3~2.7 V
  t_{pd} = 8.6 ns (max) at V_{CC} = 1.8 V
- High-level output current:
  I_{OH}/I_{OL} = ±24 mA (min) at V_{CC} = 3.0 V
  I_{OH}/I_{OL} = ±18 mA (min) at V_{CC} = 2.3 V
  I_{OH}/I_{OL} = ±6 mA (min) at V_{CC} = 1.8 V
- 3.6-V tolerant inputs
- 3.6-V power down protection outputs



SSOP6-P-0.65A

Weight: 0.0068 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Value	Unit
Power supply voltage	V_{CC}	−0.5~4.6	V
DC input voltage	V_{IN}	−0.5~4.6	V
DC output voltage	V_{OUT}	−0.5~4.6 (Note 1)	V
		−0.5~V_{CC} + 0.5 (Note 2)	
Input diode current	I_{IK}	−50	mA
Output diode current	I_{OK}	−50 (Note 3)	mA
DC output current	I_{OUT}	±50	mA
Power dissipation	P_D	200	mW
DC V_{CC}/ground current	I_{CC}	±100	mA
Storage temperature	T_{stg}	−65~150	°C

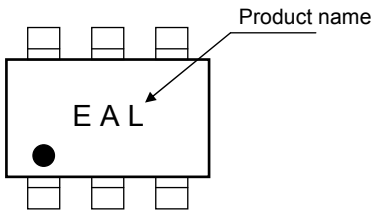
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: V_{CC} = 0 V

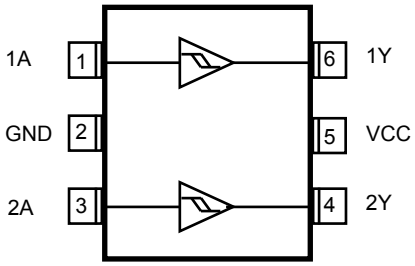
Note 2: High or Low state. I_{OUT} absolute maximum rating must be observed.

Note 3: V_{OUT} < GND

Marking



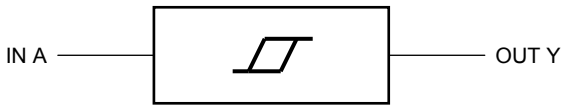
Pin Assignment (top view)



Truth Table

A	Y
L	L
H	H

IEC Logic Symbol



Operating Ranges

Characteristics	Symbol	Value		Unit
Power supply voltage	V_{CC}	1.8~3.6		V
		1.2~3.6	(Note 4)	
Input voltage	V_{IN}	−0.3~3.6		V
Output voltage	V_{OUT}	0~3.6	(Note 5)	V
		0~V_{CC}	(Note 6)	
Output Current	I_{OH}/I_{OL}	±24	(Note 7)	mA
		±18	(Note 8)	
		±6	(Note 9)	
Operating temperature	T_{opr}	−40~85		°C

Note 4: Data retention only

Note 5: V_{CC} = 0 V

Note 6: High or Low state

Note 7: V_{CC} = 3.0~3.6 V

Note 8: V_{CC} = 2.3~2.7 V

Note 9: V_{CC} = 1.8 V

DC Electrical Characteristics (Ta = −40~85°C, 2.7 V < V_{CC} ≦ 3.6 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Threshold voltage	High level	V_P	—		3.6	-	2.2	V
					3.0	-	2.0	
	Low level	V_N	—		3.6	0.8	-	V
					3.0	0.7	-	
Hysteresys Voltage		V_H	—		3.6	0.3	1.2	V
					3.0	0.3	1.2	
High-Level Output Voltage		V_{OH}	V_{IN} = V_{IH}	I_{OH} = −100 μA	2.7~3.6	V_{CC} − 0.2	—	V
				I_{OH} = −12 mA	2.7	2.2	—	
				I_{OH} = −18 mA	3.0	2.4	—	
				I_{OH} = −24 mA	3.0	2.2	—	
Low-Level Output Voltage		V_{OL}	V_{IN} = V_{IL}	I_{OL} = 100 μA	2.7~3.6	—	0.2	
				I_{OL} = 12 mA	2.7	—	0.4	
				I_{OL} = 18 mA	3.0	—	0.4	
				I_{OL} = 24 mA	3.0	—	0.55	
Input Leakage Current		I_{IN}	V_{IN} = 0~3.6 V		2.7~3.6	—	±5.0	μA
Power-off Leakage Current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent Supply Current		I_{CC}	V_{IN} = V_{CC} or GND		2.7~3.6	—	20.0	μA
			V_{CC} ≦ (V_{IN}, V_{OUT}) ≦ 3.6 V		2.7~3.6	—	±20.0	
Increase in I_{CC} per Input		ΔI_{CC}	V_{IH} = V_{CC} − 0.6 V		2.7~3.6	—	750	

DC Electrical Characteristics (Ta = −40~85°C, 2.3 V ≦ V_{CC} ≦ 2.7 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Threshold voltage	High level	V_P	—		2.3	-	1.8	V
	Low level	V_N	—		2.3	0.5	-	
Hysteresys Voltage		V_H	—		2.3	0.3	1.0	V
High-Level Output Voltage		V_{OH}	V_{IN} = V_{IH}	I_{OH} = −100 μA	2.3~2.7	V_{CC} − 0.2	—	V
				I_{OH} = −6 mA	2.3	2.0	—	
				I_{OH} = −12 mA	2.3	1.8	—	
				I_{OH} = −18 mA	2.3	1.7	—	
Low-Level Output Voltage		V_{OL}	V_{IN} = V_{IL}	I_{OL} = 100 μA	2.3~2.7	—	0.2	
				I_{OL} = 12 mA	2.3	—	0.4	
				I_{OL} = 18 mA	2.3	—	0.6	
Input Leakage Current		I_{IN}	V_{IN} = 0~3.6 V		2.3~2.7	—	±5.0	μA
Power-off Leakage Current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent Supply Current		I_{CC}	V_{IN} = V_{CC} or GND		2.3~2.7	—	20.0	μA
			V_{CC} ≦ (V_{IN}, V_{OUT}) ≦ 3.6 V		2.3~2.7	—	±20.0	

DC Electrical Characteristics (Ta = –40~85°C, 1.8 V ≦ V_{CC} < 2.3 V)

Characteristics		Symbol	Test Condition		V_{CC} (V)	Min	Max	Unit
Threshold voltage	High level	V_P	—		1.8	-	1.4	V
	Low level	V_N	—		1.8	0.25	-	
Hysteresys Voltage		V_H	—		1.8	0.2	0.95	V
High-Level Output Voltage		V_{OH}	V_{IN} = V_{IH}	I_{OH} = –100 μA	1.8	V_{CC} – 0.2	—	V
				I_{OH} = –6 mA	1.8	1.4	—	
Low-Level Output Voltage		V_{OL}	V_{IN} = V_{IL}	I_{OL} = 100 μA	1.8	—	0.2	
				I_{OL} = 6 mA	1.8	—	0.3	
Input Leakage Current		I_{IN}	V_{IN} = 0~3.6 V		1.8	—	±5.0	μA
Power-off Leakage Current		I_{OFF}	V_{IN}, V_{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent Supply Current		I_{CC}	V_{IN} = V_{CC} or GND		1.8	—	20.0	μA
			V_{CC} ≦ (V_{IN}, V_{OUT}) ≦ 3.6 V		1.8	—	±20.0	

AC Electrical Characteristics (Ta = –40~85°C, input t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω)

Characteristics	Symbol	Test Condition	V_{CC} (V)	Min	Max	Unit
Propagation delay time	t_{pLH} t_{pHL}	(Figure 1 and 2)	1.8	1.0	8.6	ns
			2.5 ± 0.2	0.8	4.3	
			3.3 ± 0.3	0.6	4.0	

For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

Dynamic Switching Characteristics (Ta = 25°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition	V_{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V_{OL}	V_{OLP}	V_{IN} = 1.8 V, V_{IL} = 0 V (Note 10)	1.8	0.25	ns
		V_{IN} = 2.5 V, V_{IL} = 0 V (Note 10)	2.5	0.6	
		V_{IN} = 3.3 V, V_{IL} = 0 V (Note 10)	3.3	0.8	
Quiet output minimum dynamic V_{OL}	V_{OLV}	V_{IN} = 1.8 V, V_{IL} = 0 V (Note 10)	1.8	−0.25	ns
		V_{IN} = 2.5 V, V_{IL} = 0 V (Note 10)	2.5	−0.6	
		V_{IN} = 3.3 V, V_{IL} = 0 V (Note 10)	3.3	−0.8	
Quiet output minimum dynamic V_{OH}	V_{OHV}	V_{IN} = 1.8 V, V_{IL} = 0 V (Note 10)	1.8	1.5	ns
		V_{IN} = 2.5 V, V_{IL} = 0 V (Note 10)	2.5	1.9	
		V_{IN} = 3.3 V, V_{IL} = 0 V (Note 10)	3.3	2.2	

Note 10: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	V_{CC} (V)	TYP.	Unit
Input Capacitance	C_{IN}	—	1.8, 2.5, 3.3	4	pF
Power Dissipation Capacitance	C_{PD}	f_{IN} = 10 MHz (Note 11)	1.8, 2.5, 3.3	27	pF

Note 11: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation:
$I_{CC\ (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$

AC Test Circuit

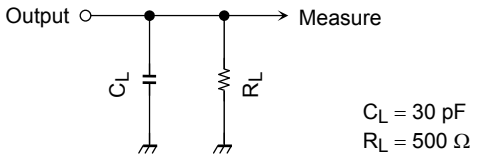
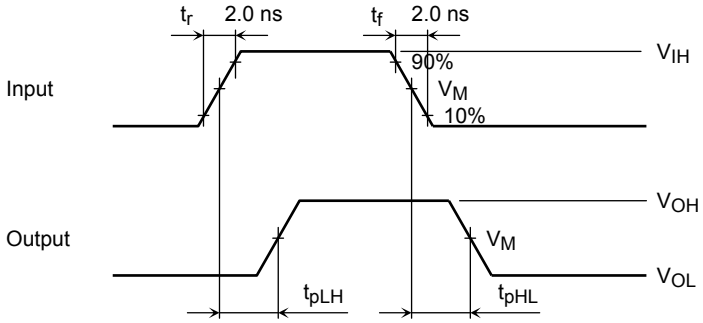


Figure 1

AC Waveforms



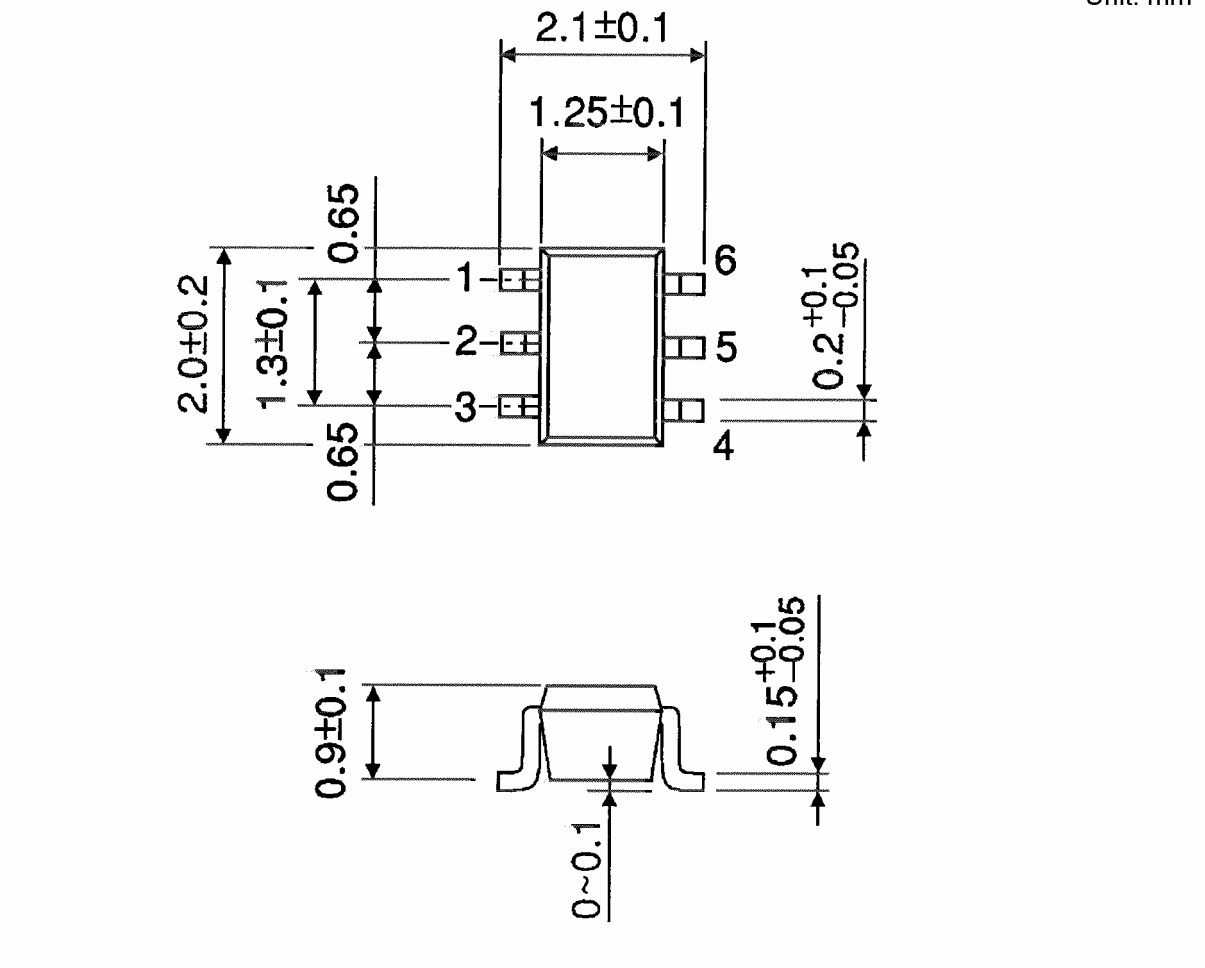
Symbol	V_{CC}		
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$

Figure 2 t_{pLH}, t_{pHL}

Package Dimensions

SSOP6-P-0.65A

Unit: mm



Weight: 0.0068 g (typ.)

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20070701-EN GENERAL

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